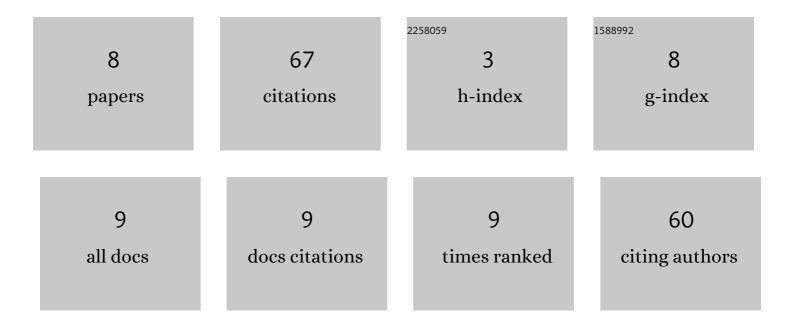
Huanhuan Wang

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/12053671/publications.pdf Version: 2024-02-01



HUANHUAN WANC

#	Article	IF	CITATIONS
1	Simulation of Grazing-Incidence Synchrotron X-ray Topographic Images of Threading c+a Dislocations in 4H-SiC. Materials Research Society Symposia Proceedings, 2012, 1433, 53.	0.1	23
2	Analysis of Dislocation Behavior in Low Dislocation Density, PVT-Grown, Four-Inch Silicon Carbide Single Crystals. Materials Research Society Symposia Proceedings, 2010, 1246, 1.	0.1	18
3	Cupric oxide nanowires assembled by nanoparticles in situ with enhancing electrocatalytic oxidation of ascorbic acid. Applied Surface Science, 2014, 292, 291-296.	6.1	8
4	Quantitative Comparison Between Dislocation Densities in Offcut 4H-SiC Wafers Measured Using Synchrotron X-ray Topography and Molten KOH Etching. Journal of Electronic Materials, 2013, 42, 794-798.	2.2	5
5	Characterization of V-shaped Defects in 4H-SiC Homoepitaxial Layers. Journal of Electronic Materials, 2015, 44, 1293-1299.	2.2	4
6	Characterization and Formation Mechanism of Six Pointed Star-Type Stacking Faults in 4H-SiC. Journal of Electronic Materials, 2013, 42, 787-793.	2.2	3
7	Direct Observation of Stacking Fault Nucleation from Deflected Threading Dislocations with Burgers Vector c+a in PVT Grown 4H-SiC. Materials Research Society Symposia Proceedings, 2014, 1693, 49.	0.1	3
8	A method to determine fault vectors in 4H-SiC from stacking sequences observed on high resolution transmission electron microscopy images. Journal of Applied Physics, 2014, 116, 104905.	2.5	2